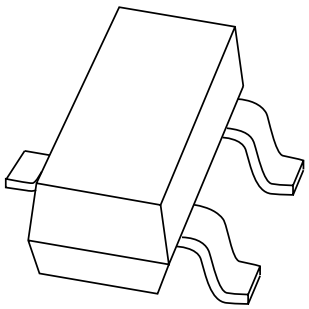
DATA SHEET



MMBT3904
NPN switching transistor

Product data sheet
Supersedes data of 2002 Oct 04

2004 Feb 03

NPN switching transistor MMBT3904

FEATURES

- Collector current capability I_C = 200 mA
- Collector-emitter voltage V_{CEO} = 40 V.

APPLICATIONS

- General switching and amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complement: MMBT3906.

MARKING

TYPE NUMBER	MARKING CODE(1)
MMBT3904	7A∗

Note

1. ∗ = p: Made in Hong Kong.
   ∗ = t: Made in Malaysia.
   ∗ = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I_C	collector current (DC)	200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

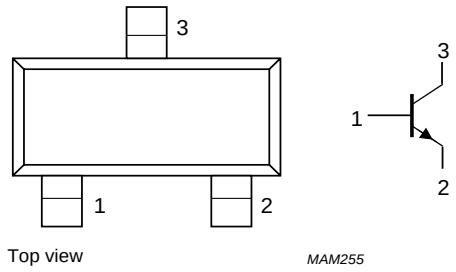


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
MMBT3904	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	200	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

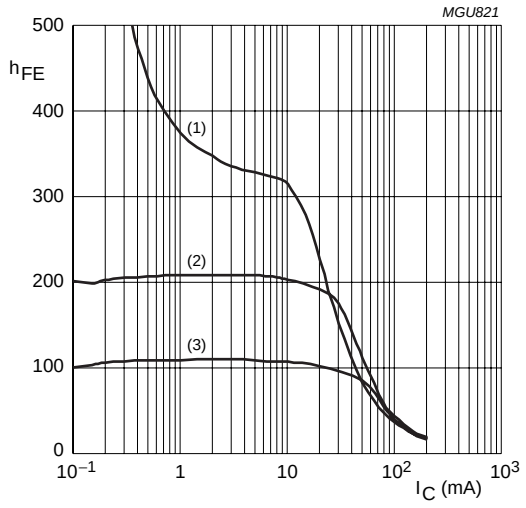
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 30 V	–	50	nA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 6 V	–	50	nA
h_{FE}	DC current gain	V_{CE} = 1 V; see Fig.2; note 1			
		I_C = 0.1 mA	60	–	
		I_C = 1 mA	80	–	
		I_C = 10 mA	100	300	
		I_C = 50 mA	60	–	
		I_C = 100 mA	30	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 10 mA; I_B = 1 mA	–	200	mV
		I_C = 50 mA; I_B = 5 mA	–	300	mV
V_{BEsat}	base-emitter saturation voltage	I_C = 10 mA; I_B = 1 mA	650	850	mV
		I_C = 50 mA; I_B = 5 mA	–	950	mV
C_c	collector capacitance	$I_E = I_e$ = 0; V_{CB} = 5 V; f = 1 MHz	–	4	pF
C_e	emitter capacitance	$I_C = I_c$ = 0; V_{BE} = 500 mV; f = 1 MHz	–	8	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = 20 V; f = 100 MHz	300	–	MHz
F	noise figure	I_C = 100 μA; V_{CE} = 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	–	5	dB
Switching times (between 10% and 90% levels); see Fig.3					
t_d	delay time	I_{Con} = 10 mA; I_{Bon} = 1 mA; I_{Boff} = −1 mA	–	35	ns
t_r	rise time		–	35	ns
t_s	storage time		–	200	ns
t_f	fall time		–	50	ns

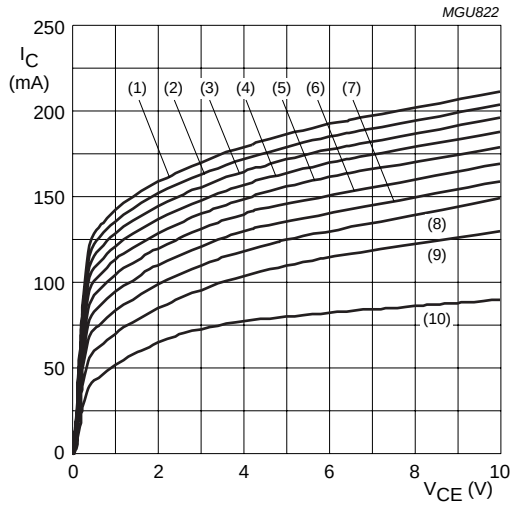
Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



V_{CE} = 1 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

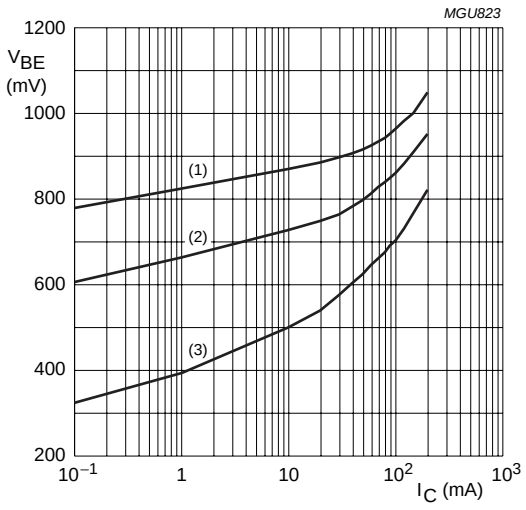
Fig.2 DC current gain; typical values.



T_{amb} = 25 °C.

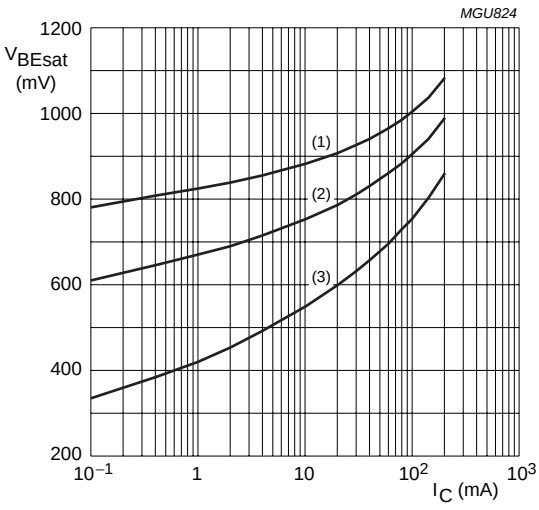
(1) I_B = 5 mA.
(2) I_B = 4.5 mA.
(3) I_B = 4 mA.
(4) I_B = 3.5 mA.
(5) I_B = 3 mA.
(6) I_B = 2.5 mA.
(7) I_B = 2 mA.
(8) I_B = 1.5 mA.
(9) I_B = 1 mA.
(10) I_B = 0.5 mA.

Fig.3 Collector current as a function of collector-emitter voltage.



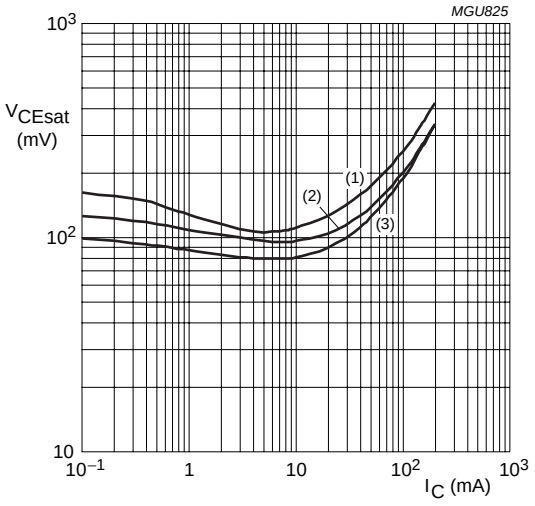
V_{CE} = 1 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.4 Base-emitter voltage as a function of collector current.



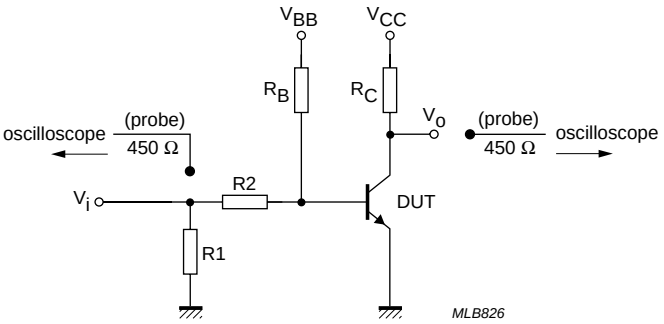
I_C/I_B = 10.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.5 Base-emitter saturation voltage as a function of collector current.



$I_C/I_B = 10$.
(1) $T_{amb} = 150$ °C.
(2) $T_{amb} = 25$ °C.
(3) $T_{amb} = -55$ °C.

Fig.6 Collector-emitter saturation voltage as a function of collector current.

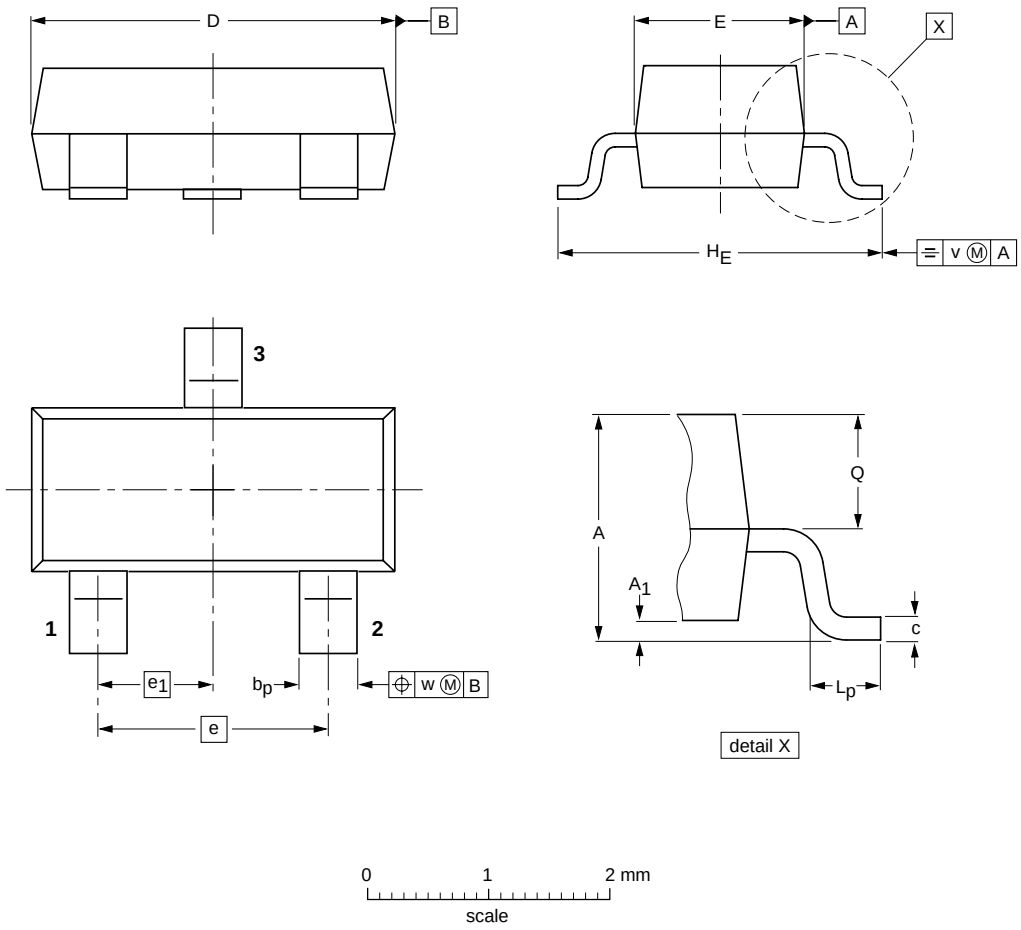


$V_i = 5$ V; T = 500 μs; $t_p = 10$ μs; $t_r = t_f \leq 3$ ns.
R1 = 56 Ω; R2 = 2.5 kΩ; $R_B = 3.9$ kΩ; $R_C = 270$ Ω.
$V_{BB} = -1.9$ V; $V_{CC} = 3$ V.
Oscilloscope: input impedance $Z_i = 50$ Ω.

Fig.7 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				~~04-11-04~~ 06-03-16